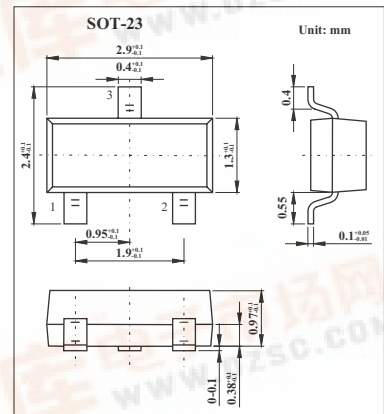


SMD Type Diodes

Silicon Schottky Diodes
BAS125 series

■ Features

- For low-loss, fast-recovery, meter protection, bias isolation and clamping applications
- Integrated diffused guard ring
- Low forward voltage



■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Conditions	Values	Unit
Reverse voltage	V _R		25	V
Forward current	I _F		100	mA
Surge forward current	I _{FRM}	t ≤ 10 ms	500	mA
Total power dissipation	P _{tot}	T _s < 25 °C (Note 3)	250	mW
Junction temperature	T _j		150	°C
Storage temperature range	T _{stg}		-55 to +150	°C
Junction-ambient	R _{th JA}	Note 2	< 725	K/W
Junction-soldering point	R _{th JS}		< 565	K/W

Note

1. For detailed information see chapter Package Outlines.
2. Package mounted on alumina 15 mm × 16.7 mm × 0.7 mm.
3. 450 mW per package.

Silicon Schottky Diodes

BAS125 series

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse voltage	I_R	$V_R = 20\text{ V}$			1	$\mu\text{ A}$
		$V_R = 25\text{ V}$			10	
Forward voltage	V_F	$I_F = 1\text{ mA}$		385	410	mV
		$I_F = 10\text{ mA}$		530		
		$I_F = 35\text{ mA}$		800	900	
Diode capacitance	C_T	$V_R = 0, f = 10\text{ kHz}$			1.1	pF
Differential forward resistance	R_F	$I_F = 5\text{ mA}, f = 10\text{ kHz}$		15		Ω

■ Marking

Type	BAS125	BAS125-04	BAS125-05	BAS125-06
Marking	13	14	15	16